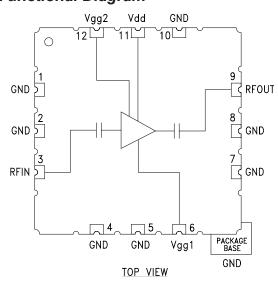


Typical Applications

The HMC463LH250 is ideal for:

- Telecom Infrastructure
- Microwave Radio & VSAT
- Military EW, ECM & C3I
- Test Instrumentation
- Fiber Optics

Functional Diagram



Features

50 Ohm Matched Input/Output

Hermetic SMT Package

Gain: 14 dB

Noise Figure: 2.5 dB @ Mid-Band

P1dB Output Power: +18 dBm @ Mid-Band

Supply Voltage: +5V @ 60mA

Screening to MIL-PRF-38535 (Class B or S) Available

General Description

The HMC463LH250 is a GaAs MMIC pHEMT Low Noise AGC Distributed Amplifier packaged in a hermetic surface mount package which operates between 2 and 20 GHz. The amplifier provides 13 dB of gain, 3 dB noise figure and 18 dBm of output power at 1 dB gain compression while requiring only 60 mA from a +5V supply. An optional gate bias (Vgg2) is provided to allow Adjustable Gain Control (AGC) of 8 dB typical. Gain flatness is excellent at ±0.5 dB from 2 - 14 GHz making the HMC463LH250 ideal for EW, ECM RADAR, test equipment and High-Reliability applications. The HMC463LH250 LNA I/Os are internally matched to 50 Ohms and are internally DC blocked.

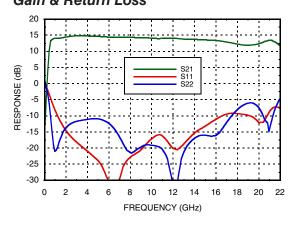
Electrical Specifications, $T_A = +25^{\circ}$ C, Vdd=5V, Vgg2= Open, Idd=60 mA^*

Parameter	Min.	Тур.	Max.	Min.	Тур.	Max.	Min.	Тур.	Max.	Units
Frequency Range	2.0 - 6.0		6.0 - 16.0		16.0 - 20.0			GHz		
Gain	11.5	14.5		9	12		8	11		dB
Gain Flatness		±0.25			±0.5			±0.9		dB
Gain Variation Over Temperature		0.010			0.010			0.010		dB/ °C
Noise Figure		3.5	5.5		2.5	4.5		4	5.5	dB
Input Return Loss		15			15			9		dB
Output Return Loss		11			15			7		dB
Output Power for 1 dB Compression (P1dB)	16	19		13	18		10	13		dBm
Saturated Output Power (Psat)		21.5			20.5			19		dBm
Output Third Order Intercept (IP3)		29			27			24		dBm
Supply Current (Idd) (Vdd= 5V, Vgg1= -0.9V Typ.)		60	80		60	80		60	80	mA

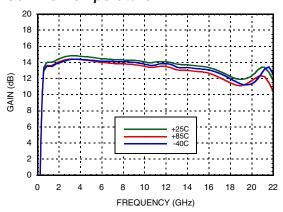
^{*} Adjust Vgg1 between -2 to -0V to achieve Idd= 60 mA typical.



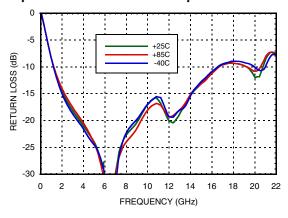
Gain & Return Loss



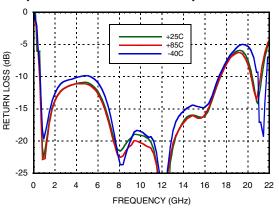
Gain vs. Temperature



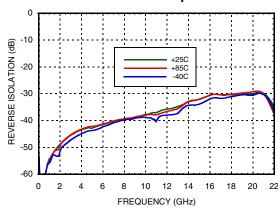
Input Return Loss vs. Temperature



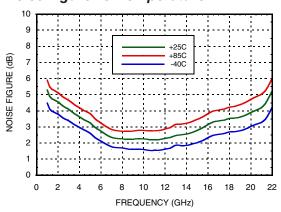
Output Return Loss vs. Temperature



Reverse Isolation vs. Temperature

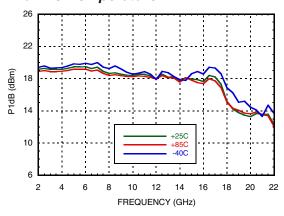


Noise Figure vs. Temperature

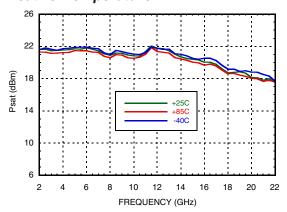




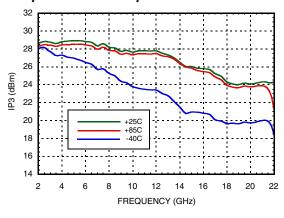
P1dB vs. Temperature



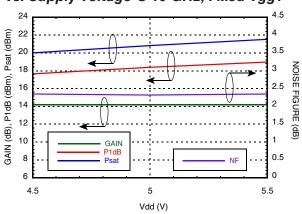
Psat vs. Temperature



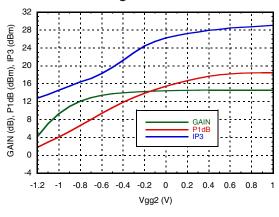
Output IP3 vs. Temperature



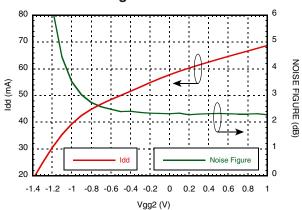
Gain, Power & Noise Figure vs. Supply Voltage @ 10 GHz, Fixed Vgg1



Gain, P1dB & Output IP3 vs. Control Voltage @ 10 GHz



Noise Figure & Supply Current vs. Control Voltage @ 10 GHz

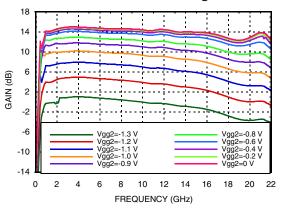




/06.1217

GaAs pHEMT MMIC LOW NOISE AGC AMPLIFIER, 2 - 20 GHz

Gain @ Several Control Voltages





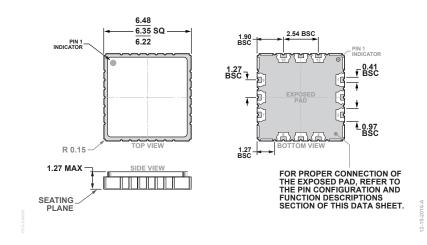
Absolute Maximum Ratings

Drain Bias Voltage (Vdd)	+9 V
Gate Bias Voltage (Vgg1)	-2 to 0 Vdc
Gate Bias Current (Igg1)	2.5 mA
Gate Bias Voltage (Vgg2)(AGC)	(Vdd -9) Vdc to +2 Vdc
RF Input Power (RFIN)(Vdd = +5 V)	+18 dBm
Channel Temperature	175 °C
Storage Temperature	-65 to +150 °C
Operating Temperature	-40 to +85 °C
ESD Sensitivity (HBM)	Class 0B - Passed 150V

Typical Supply Current vs. Vdd

Vdd (V)	Idd (mA)
+4.5	58
+5.0	60
+5.5	62

Outline Drawing



12-Terminal Ceramic Leadless Chip Carrier [LCC] (E-12-2)

Dimensions shown in millimeters.

Package Information

Part Number	Package Body Material	Lead Finish	MSL Rating	Package Marking [2]
HMC463LH250	Ceramic & Kovar	Au	MSL1 [1]	H463 XXXX

^[1] Max peak reflow temperature of 250 $^{\circ}\text{C}$

^{[2] 4-}Digit lot number XXXX



/06 1217

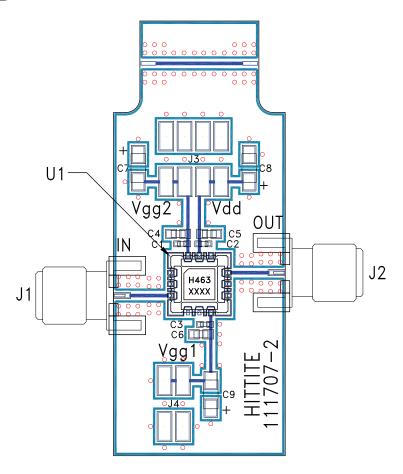
GaAs pHEMT MMIC LOW NOISE AGC AMPLIFIER, 2 - 20 GHz

Pin Descriptions

Pin Number	Function	Description	Interface Schematic	
1, 2, 4, 5, 7, 8, 10	GND	Ground paddle must be connected to RF/DC ground.	Ģ GND =	
3	RFIN	This pad is AC coupled and matched to 50 Ohms.	RFIN ○── ├──	
6	Vgg1	Gate control for amplifier. Adjust to achieve Idd= 60 mA.	Vgg10	
9	RFOUT	This pad is AC coupled and matched to 50 Ohms.	— —○ RFOUT	
11	Vdd	Power supply voltage for the amplifier. External bypass capacitors are required	Vdd —	
12	Vgg2	Optional gate control if AGC is required. Leave Vgg2 open circuited if AGC is not required.	Vgg2	



Evaluation PCB



List of Materials for Evaluation PCB 111709 [1]

Item	Description
J1 - J2	SRI K Connector
J3 - J4	2 mm Molex Header
C1 - C3	100 pF Capacitor, 0402 Pkg.
C4 - C6	1000 pF Capacitor, 0603 Pkg.
C7 - C9	4.7 μF Capacitor, Tantalum
U1	HMC463LH250
PCB [2]	111707 Evaluation PCB

[1] Reference this number when ordering complete evaluation PCB

[2] Circuit Board Material: Rogers 4350

The circuit board used in the application should use RF circuit design techniques. Signal lines should have 50 Ohm impedance while the package ground leads and package bottom should be connected directly to the ground plane similar to that shown. A sufficient number of via holes should be used to connect the top and bottom ground planes. The evaluation board should be mounted to an appropriate heat sink. The evaluation circuit board shown is available from Analog Devices upon request.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for RF Development Tools category:

Click to view products by Analog Devices manufacturer:

Other Similar products are found below:

MAAM-011117 MAAP-015036-DIEEV2 EV1HMC1113LP5 EV1HMC6146BLC5A EV1HMC637ALP5 EVAL-ADG919EBZ ADL5363EVALZ LMV228SDEVAL SKYA21001-EVB SMP1331-085-EVB EV1HMC618ALP3 EVAL01-HMC1041LC4 MAAL-011111-000SMB
MAAM-009633-001SMB MASW-000936-001SMB 107712-HMC369LP3 107780-HMC322ALP4 SP000416870 EV1HMC470ALP3
EV1HMC520ALC4 EV1HMC244AG16 MAX2614EVKIT# 124694-HMC742ALP5 SC20ASATEA-8GB-STD MAX2837EVKIT+
MAX2612EVKIT# MAX2692EVKIT# EV1HMC629ALP4E SKY12343-364LF-EVB 108703-HMC452QS16G EV1HMC863ALC4
EV1HMC427ALP3E 119197-HMC658LP2 EV1HMC647ALP6 ADL5725-EVALZ 106815-HMC441LM1 EV1HMC1018ALP4
UXN14M9PE MAX2016EVKIT EV1HMC939ALP4 MAX2410EVKIT MAX2204EVKIT+ EV1HMC8073LP3D SIMSA868-DKL
SIMSA868C-DKL SKY65806-636EK1 SKY68020-11EK1 SKY67159-396EK1 SKY66181-11-EK1 SKY65804-696EK1